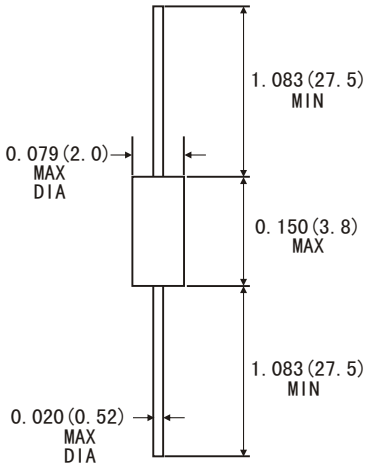
DB3
Bidirectional Trigger Diode

Features

- Bilateral triggering device
- Glass passivated chip junctions
- low breakover current
- Long-term reliability
- Parameter stability
- High temperature soldering
  260℃/10 seconds at terminals
- Component in accordance to
  RoHS 2002/95/1 and WEEE 2002/96/EC

DO-35(GLASS)



Dimensions in inches and (millimeters)

Mechanical Date

- **Case:** Glass,hermetically sealed
- **Terminals:** Plated axial leads solderable per
  MIL-STD 202E, method 208C
- Mounting position: Any

Absolute Maximum Ratings

	Symbol	DB3	UNIT
Power dissipation	P_C	150	mW
Repetitive peak on-state current @tp=20μS、F=100Hz	I_{TRM}	2.0	A
Operating junction temperature at tp<1s,T_A=25℃	T_J	-40 ~ 125	℃
Storage temperature	T_{STG}	-40 ~ 125	℃

Electrical Characteristics

(T_A = 25 °C unless otherwise noted)

	Symbol	DB3	UNIT
Breakover voltage(See Fig.1)	V_{BO}	28	V
		32	V
		36	V
Breakover voltage Symmetry(See Fig.1)	$\triangle V_{BO}$	3.0	V
Minimum dynamic breakover voltage@ I_{BO} to I_F=10mA(See Fig.1)	$\triangle V$	5.0	V
Minimum output voltage(See Fig.2)	V_O	5.0	V
Maximum breakover current(See Fig.1)	I_{BO}	100	μA
Rise time(See Fig.3)	t_r	1.5	μS
Maximum leakage current @V_B=0.5V_{BO}(See Fig.1)	I_B	10	μA

Fig.1 Voltage-Current Characteristic Curve

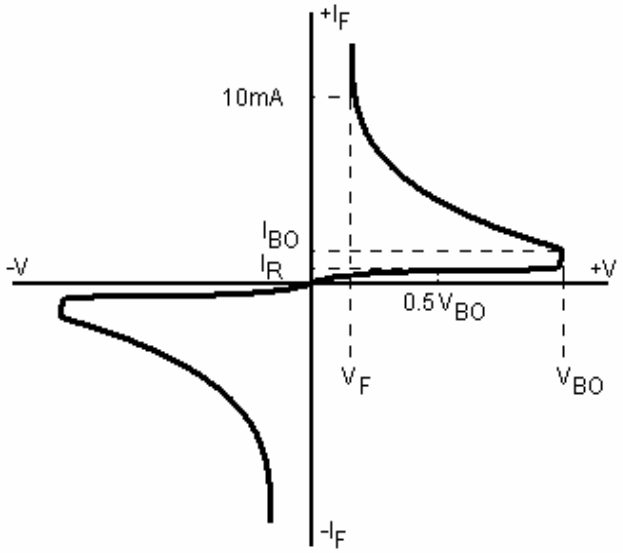


Fig.2 Test Circuit for Output Voltage

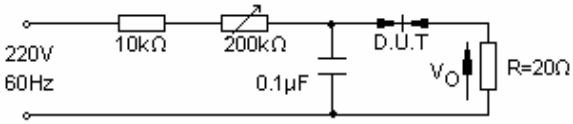


Fig.3 Test Circuit see Fig.2 Adjust R for Ip=0.5A

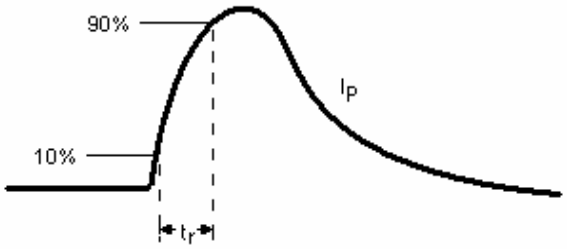


Fig.4 Power Dissipation versus Ambient Temperature (Maximum Values)

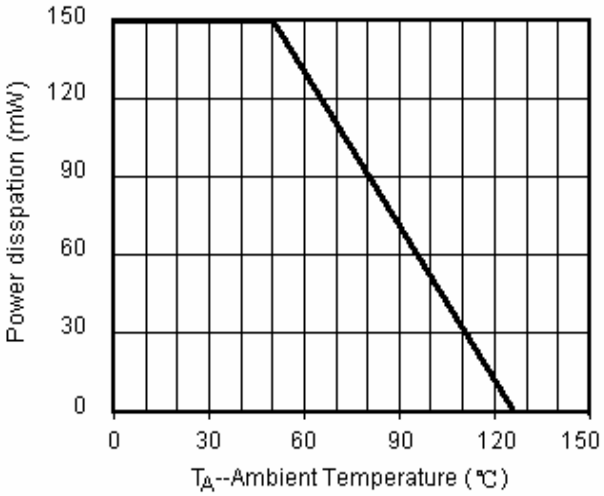


Fig.5 Repetitive Peak Pulse Current versus Pulse Duration(Maximum Values)

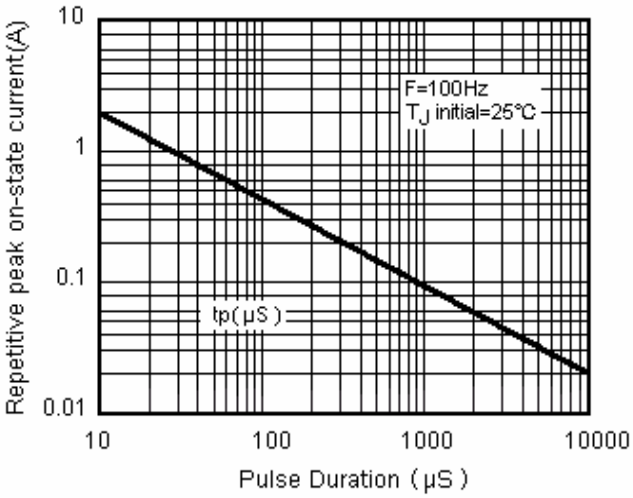


Fig.6 Relative Variation of V_{BO} versus Junction Temperature (Typical Values)